

ANGI058058-P45N

C-band matched GaN Device

Features:

Frequency: 5.8GHz

Saturated Output Power: $P_{sat} \geq 45\text{dBm}$

PowerGain: $\text{Gain} \geq 22\text{dB}$

Efficiency: $\eta = 40\%$ (type)

Port Matching: $Z_{in}/Z_{out} = 50\Omega$

Description:

ANGI058058-P45N is an internal matching GaN device, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency is 5.8GHz. This device can be used in different RF/Microwave system and subsystem.

The high output power level, high efficiency and wide operating temperature range can make application very flexible.

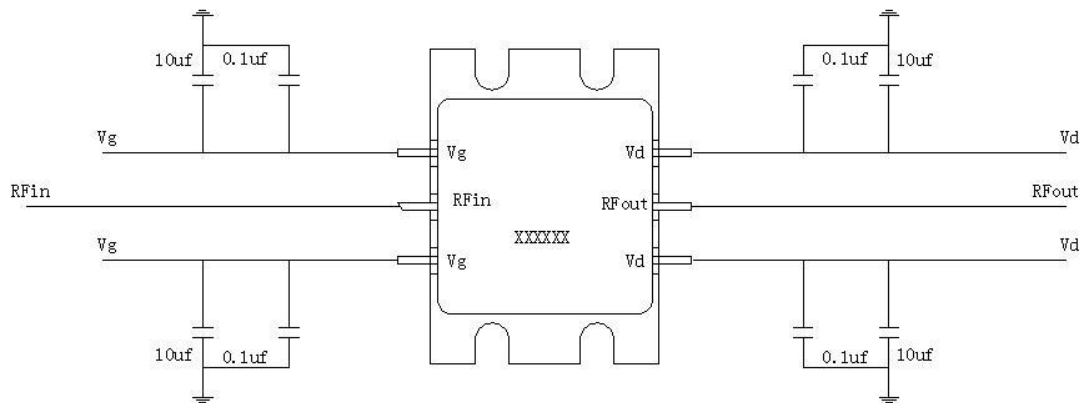
Maximun Ratings (TC=25°C, Not recommended working under this condition):

	Symbol	Value	Unit
Voltage between source and drain	V_{DS}	60	V
Voltage between gate and source	V_{GS}	-3	V
Storage Temperature Range	T_{stg}	-65 to +175	°C
Drain and Source Channel Temperature	T_{ch}	175	°C

Electrical Characteristics:

	Symbol	Test condition	Value			Unit
			Min	Typ	Max	
Drain Current	I_{dsr}	$V_{ds}=50V$ CW. $P_{in}: 23dBm$ $Freq: 5.8GHz$	-	1.5	-	A
Saturated Output Power	P_{sat}		45	-	-	dBm
Gain	G_p		22	-	-	dB
Efficiency	η		-	40	-	%

Application Circuit:



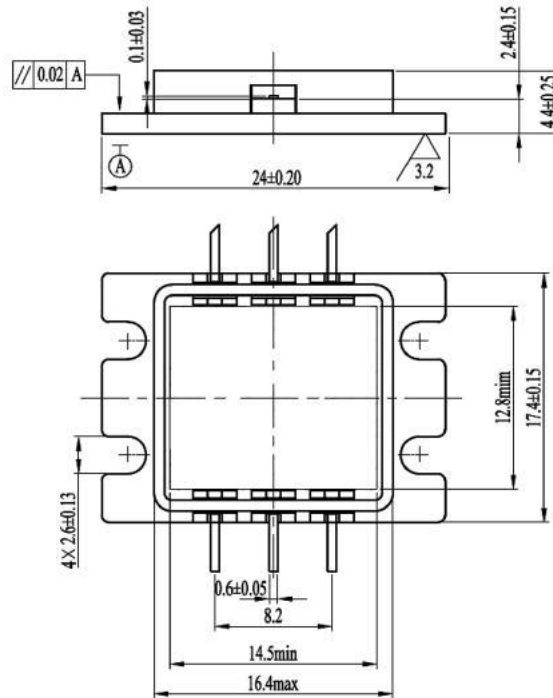
If you need more detailed product information, please contact our marketing personnel or designers.

Contact: Peter.Zhang Email: peter.zhang@anserrf.com

ESD Level:

ESD	Class III	2000V
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Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly, and wear grounding anti-static bracelet.
- When powering up, first apply grid power then add leakage.